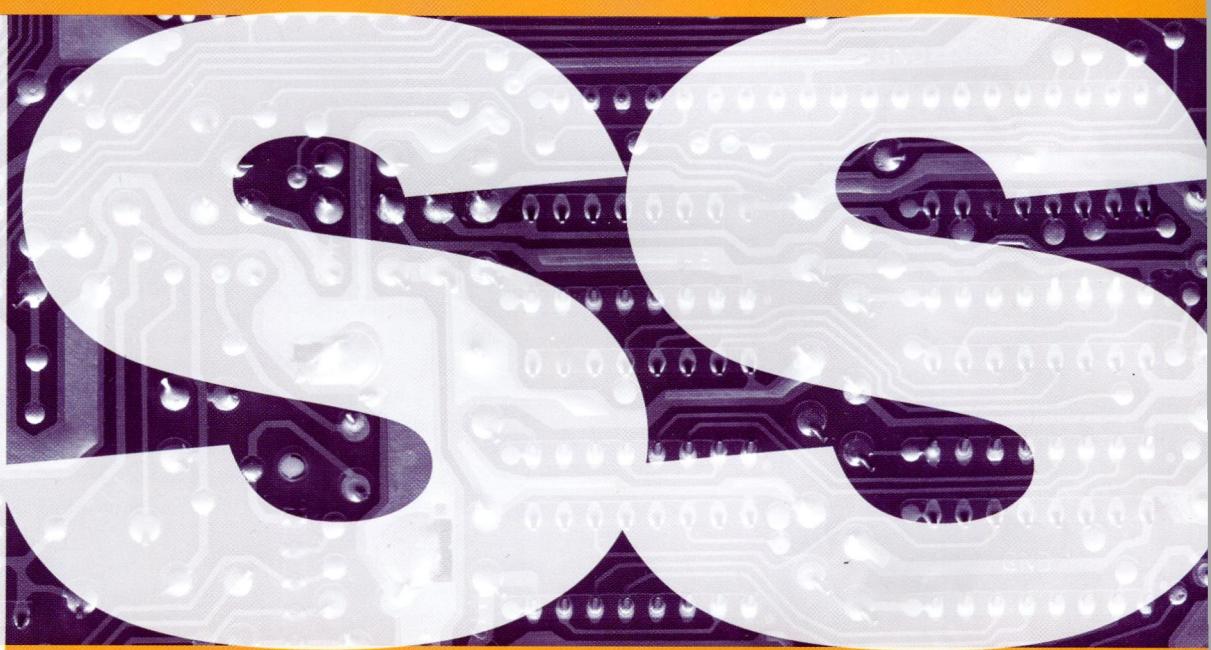


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Focus Issue on Wide Bandgap Power Semiconductors



*JSS Focus Issue on Wide Bandgap Power Semiconductors***Table of Contents****Commentary****Introduction to the Focus Issue on Wide Bandgap Power Semiconductors***Krishna Shenai, Mietek Bakowski, Noboru Ohtani* N3036**Dielectric Science and Materials****Growth and Characterization of Crack-Free Semi-Polar (1-101) GaN on 7°-off (001) Si Substrates by Metal-Organic Chemical Vapor Deposition***Hsueh-Hsing Liu, Hsien-Yu Lin, Chen-Zi Liao, Jen-Inn Chyi* N3001**Impact of the Morphological and Electrical Properties of SiO₂/4H-SiC Interfaces on the Behavior of 4H-SiC MOSFETs***Fabrizio Roccaforte, Patrick Fiorenza, Filippo Giannazzo* N3006**4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1°***Kazutoshi Kojima, Keiko Masumoto, Sachiko Ito, Akiyo Nagata, Hajime Okumura* N3012**A Thermodynamic Mechanism for PVT Growth Phenomena of SiC Single Crystals***Tatsuo Fujimoto, Noboru Ohtani, Hiroshi Tsuge, Masakazu Katsuno, Shinya Sato, Masashi Nakabayashi, Takayuki Yano* N3018**Characterization of Electrical Properties of n-Type 4H-SiC Single Crystals by Raman Spectroscopy***Xiaobo Hu, Yan Peng, Rusheng Wei, Xiufang Chen, Xiangang Xu* N3022**Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas***Hitoshi Habuka, Yusuke Fukumoto, Tomohisa Kato* N3025**Planarization of SiC and GaN Wafers Using Polishing Technique Utilizing Catalyst Surface Reaction***Yasuhisa Sano, Kenta Arima, Kazuto Yamauchi* N3028

Федеральное государственное
бюджетное учреждение науки
Центральная научная библиотека
Уральского отделения
Российской академии наук (ЦНБ УрО РАН)

Thick 4H-SiC Epitaxial Growth and Defect Reduction for Very High Voltage Bipolar Devices*Tetsuya Miyazawa, Hidekazu Tsuchida* N3036**Hydrogen Incorporation Dependence on the Thermal Growth Route in Dielectric/SiC Structures***Silma A. Corrêa, Gabriel V. Soares, Philip Tanner, Jisheng Han, Sima Dimitrijev, Fernanda C. Stedile* N3041**Gallium Nitride Crystals Grown by Hydride Vapor Phase Epitaxy with Dislocation Reduction Mechanism***Akira Usui* N3045**Progress in SiC-4H Epitaxy with Horizontal Hot Wall Reactors***M. Mauceri, A. Pecora, G. Litrico, C. Vecchio, M. Puglisi, D. Crippa* N3051**Current Status and Emerging Trends in Wide Bandgap (WBG) Semiconductor Power Switching Devices***Krishna Shenai, Michael Dudley, Robert F. Davis* N3055**Vertical Blocking Voltage Improvement of GaN HEMT Structures on n-SiC by Pre-Epitaxial Substrate Implantation***P. Kotara, R. Zhytnytska, O. Hilt, E. Cho, F. Brunner, A. Thies, E. Bahat-Treidel, J. Würfl* N3064**Growth of GaN Crystals by Na Flux Method***Yusuke Mori, Mamoru Imade, Mihoko Maruyama, Masashi Yoshimura* N3068**Improvement of Electrical Performance of HfO₂/SiO₂/4H-SiC Structure with Thin SiO₂***Chia-Ming Hsu, Jenn-Gwo Hwu* N3072**Trade-Off between Parasitic Deposition and SiC Homoepitaxial Growth Rate Using Halogenated Si-Precursors***Tangali S. Sudarshan, Tawhid Rana, Haizheng Song, M. V. S. Chandrashekhar* N3079

**HfO₂/Al₂O₃ Bilayered High-*k* Dielectric
for Passivation and Gate Insulator
in 4H-SiC Devices**

M. Usman, C. Henkel, A. Hallén N3087

**Dislocation Conversion in 4H-SiC Crystals Grown
by Metastable Solvent Epitaxy**

*Shinkichi Hamada, Hisashi Yoshioka, Hiroshi Kawami,
Nobuhiko Nakamura, Yoshitaka Setoguchi, Toru Matsunami,
Satoshi Yamaguchi, Koichi Nishikawa, Hirofumi Aoki,
Toshiyuki Isshiki, Noboru Ohtani* N3092